TECHNICAL DATA
DATA SHEET 368, REV. C

SCHOTTKY RECTIFIER
Very Low Forward Voltage

Applications:

- **Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode**

Features:

- **Soft Reverse Recovery at Low and High Temperature**
- **Low Forward Voltage Drop**
- **Low Power Loss, High Efficiency**
- **High Surge Capacity**
- **Guard Ring for Enhanced Durability and Long Term Reliability**
- **Guaranteed Reverse Avalanche Characteristics**
- **Add "C" for Ceramic Seals (SHDC) and "G" for Glidcop Leads and Ceramic Seals (SHDG)**
- **Add suffix "S" for TX/TXV screening, "SS" for JANS Screening.**

Maximum Ratings:

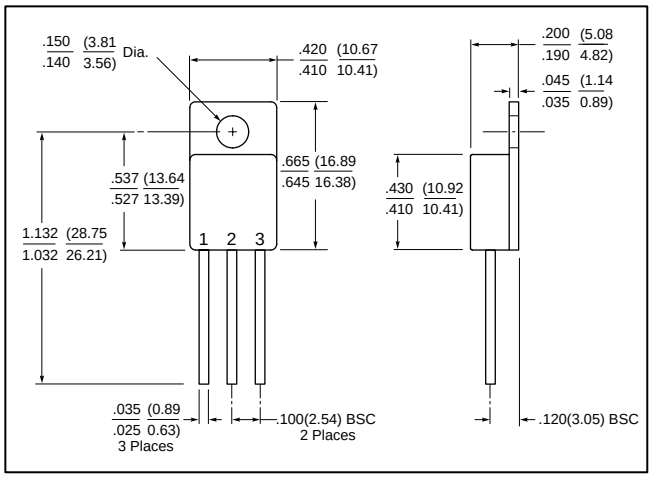
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	30	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form	16	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine wave (1) (per leg)	75	A
Max. Thermal Resistance	$R_{\theta JC}$	(per leg)	2.1	°C/W
Max. Junction Temperature	T_J	-	-65 to +150	°C
Max. Storage Temperature	T_{stg}	-	-65 to +150	°C

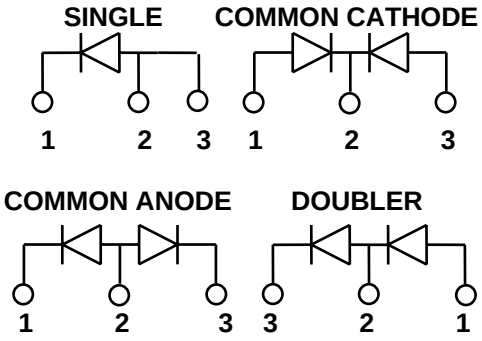
Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 16A, Pulse, T_J = 25 °C (per leg)	0.58	V
	V_{F2}	@ 16A, Pulse, T_J = 125 °C (per leg)	0.48	V
Max. Reverse Current	I_{R1}	@V_R = 30V, Pulse, T_J = 25 °C (per leg)	2.0	mA
	I_{R2}	@V_R = 30V, Pulse, T_J = 125 °C (per leg)	100	mA
Max. Junction Capacitance	C_T	@V_R = 5V, T_C = 25 °C f_{SIG} = 1MHz, V_{SIG} = 50mV (p-p) (per leg)	1100	pF

(1) in SHD package

Mechanical Dimensions: In Inches / mm





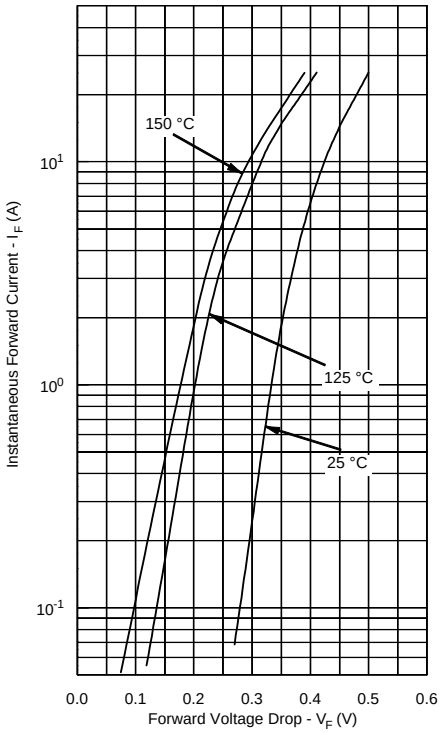
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PINOUT TABLE

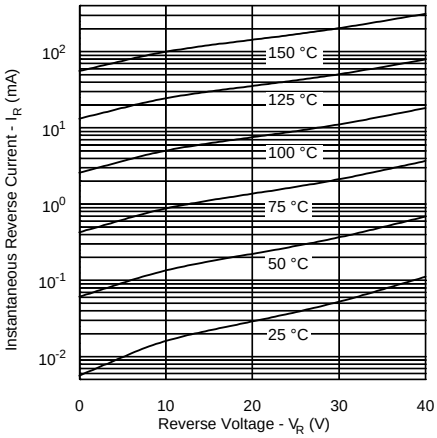
TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
DUAL RECTIFIER, COMMON CATHODE (P)	ANODE 1	COMMON CATHODE	ANODE 2
DUAL RECTIFIER, COMMON ANODE (N)	CATHODE 1	COMMON ANODE	CATHODE 2
DUAL RECTIFIER, DOUBLER (D)	ANODE	ANODE/CATHODE	CATHODE

Note: The V_f curves shown are for the SD125SA30 un-packaged die only.

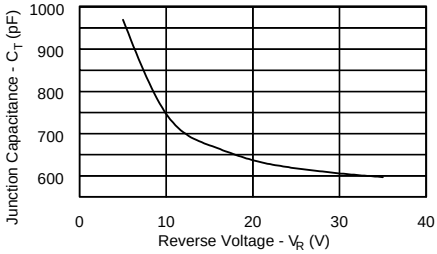
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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